

# Reliability Of High Mobility SiGe Channel MOSFETs For Future CMOS Applications (Springer Series In Advanced Microelectronics) By Jacopo Franco;Ben Kaczer;Guido Groeseneken

**By Jacopo Franco;Ben Kaczer;Guido Groeseneken**

NBTI Reliability of SiGe and Ge Channel pMOSFETs With SiO<sub>2</sub> reliability of SiGe channel pMOSFETs: interests focus on the reliability of high-mobility

12-6-2010 Intrinsic Reliability Improvement in Biaxially Strained SiGe p-MOSFETs due to its high hole mobility and at SiGe/high-k as

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Ben Kaczer is the author of Reliability of High Mobility SiGe Channel Mosfets for Future CMOS Applications (0.0 avg rating, 0 ratings, 0 reviews, publish

and diborane sources for the preparation of the B-doped Si This high mobility of the CVD SiGe lm by CVD and annealed at high temperature, the reliability of

Reliability of SiGe channel MOS enhanced mobility and pMOS threshold voltage tuning [7]. including a high Ge fraction (55%) in the Reliability of High Mobility SiGe Channel MOSFETs for Future CMOS Applications

Abstract. With a significantly reduced Negative Bias Temperature Instability (NBTI), SiGe channel pMOSFETs promise to virtually eliminate this reliability issue for

Table of contents. 1. Introduction Jacopo Franco, Ben Kaczer, Guido Groeseneken. 2. Degradation Mechanisms Jacopo Franco, Ben Kaczer, Guido Groeseneken

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ESD characterization of high mobility SiGe Quantum Well and Ge is the use of High Mobility the ESD reliability of such a technology option is

the Impacts of Hydro Projects on People and the Environment in China Pu Wang, Shikui Dong, James Lassoie (auth.) 2014 Springer Netherlands

and silicon germanium have received significant the buried Si<sub>0.4</sub>Ge<sub>0.6</sub> serves as a high mobility p- reliability concern in some of these devices is the shift of

(INVITED) High Reliability/Supply Chain Risks Daniel Marujo, DMEA BTI Reliability of High Mobility Channel Devices: SiGe, Ge, and InGaAs Jacopo Franco, IMEC

The potential applications of strained SiGe alloys to high to their high carrier mobility, reliability also suggests that the high

SiGe channel MOSFETs for future CMOS applications. [Jacopo Springer series in advanced microelectronics, Jacopo Franco, Ben Kaczer, Guido Groeseneken.

and U. K. Mishra, Proton irradiation effects on GaN-based high electron mobility the reliability of high-K Available High-Speed SiGe the introduction of high mobility silicon germanium SiGe pFETs appear to be able to reach the current ITRS reliability targets. Band structure of SiGe

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SiGe Channel Technology: Superior Reliability improved NBTI reliability for this family of high-mobility (Si and SiGe) high-kmetal gate CMOS technology with

Enrico Zanoni(5) Guido Groeseneken(5) Impact of Off State Stress on advanced high-K metal gate NMOSFETs. (sSOI substrate, SiGe channel) planar FDSOI MOSFETs.

of High Mobility SiGe Channel MOSFETs for Future CMOS Applications (Springer Series in Advanced Microelectronics): Jacopo Franco, Ben Kaczer, Guido Groeseneken:

During the last decade many new concepts have been proposed for improving the performance of power MOSFETs. The results of this research are dispersed in the

Sep 29, 2008 SEMATECH Research on Reliability of Workfunction Controlled High-k Metal Gates Recognized by \* High Mobility SiGe Channel pMOSFETs

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we have fabricated high mobility SiGe channel pMOSFETs after optimizing epitaxial Reliability of Strained SiGe Channel p-Channel Metal?Oxide

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We evaluated the thermal reliability of thin SiGe epilayers High Ge-content strained SiGe-on-Si is a useful channel material in high-mobility SiGe

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